

FIG. 1

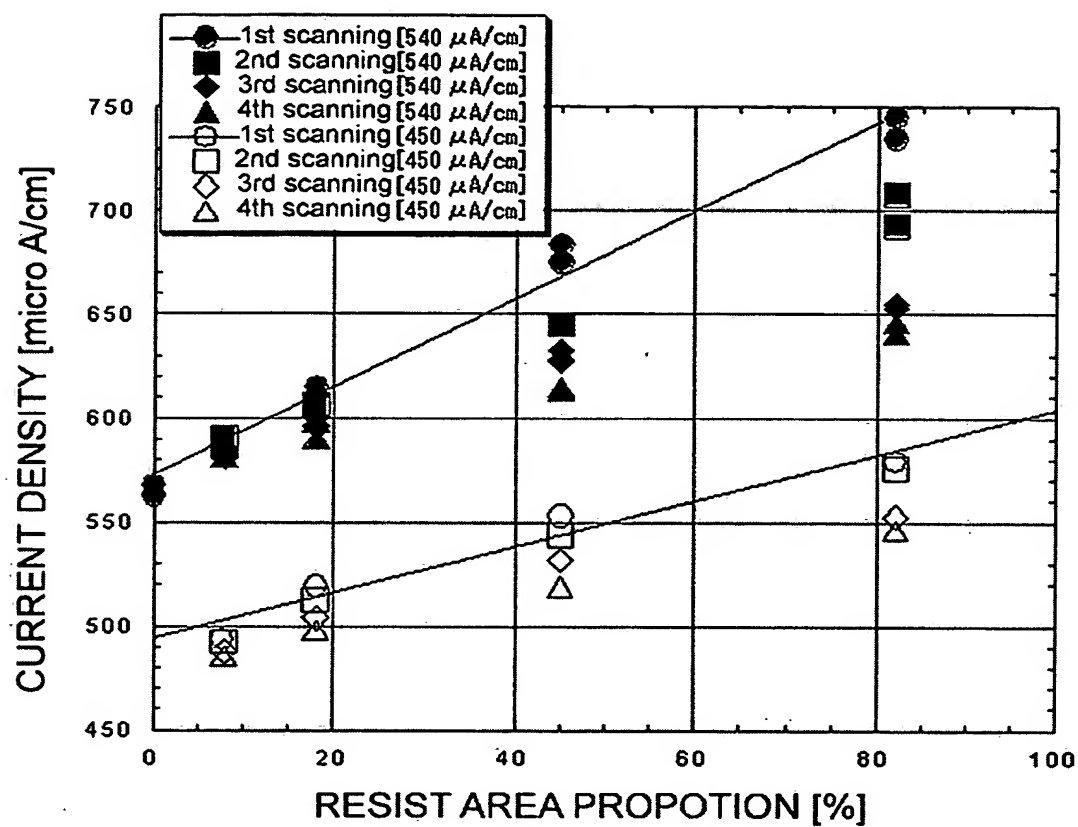


FIG. 2

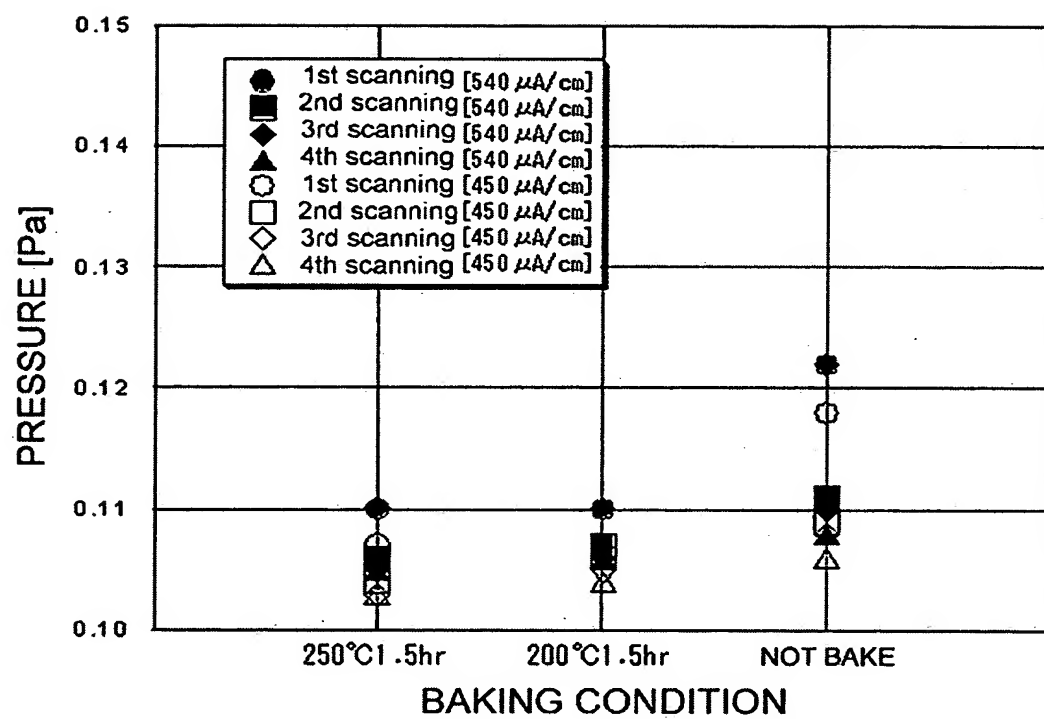


FIG. 3

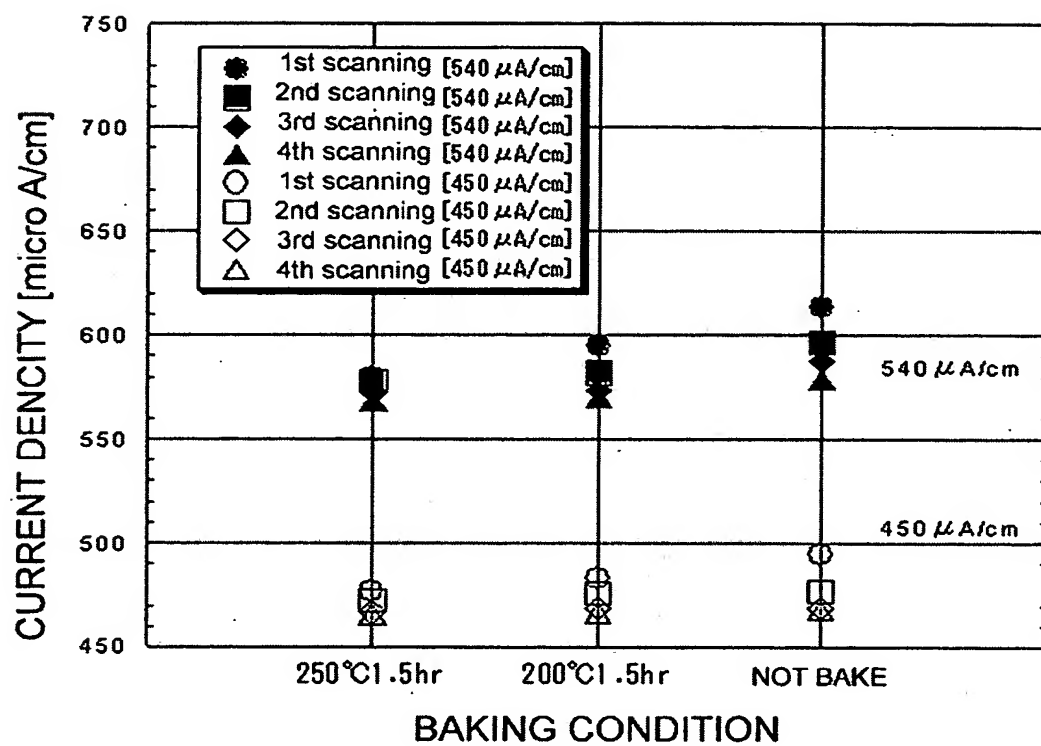
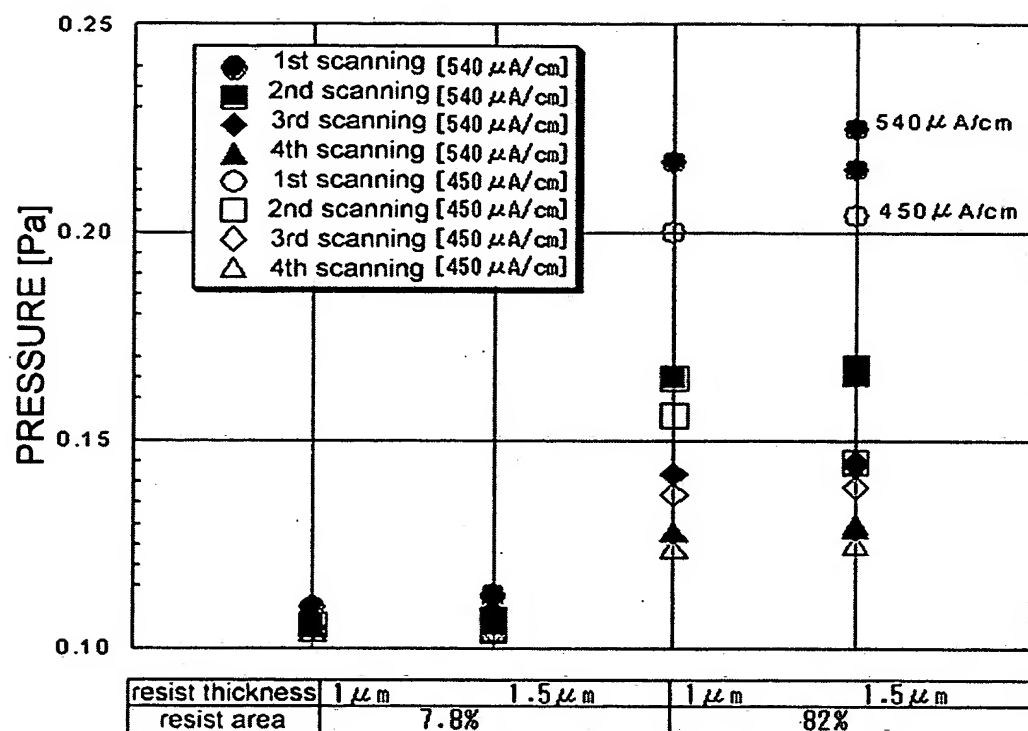
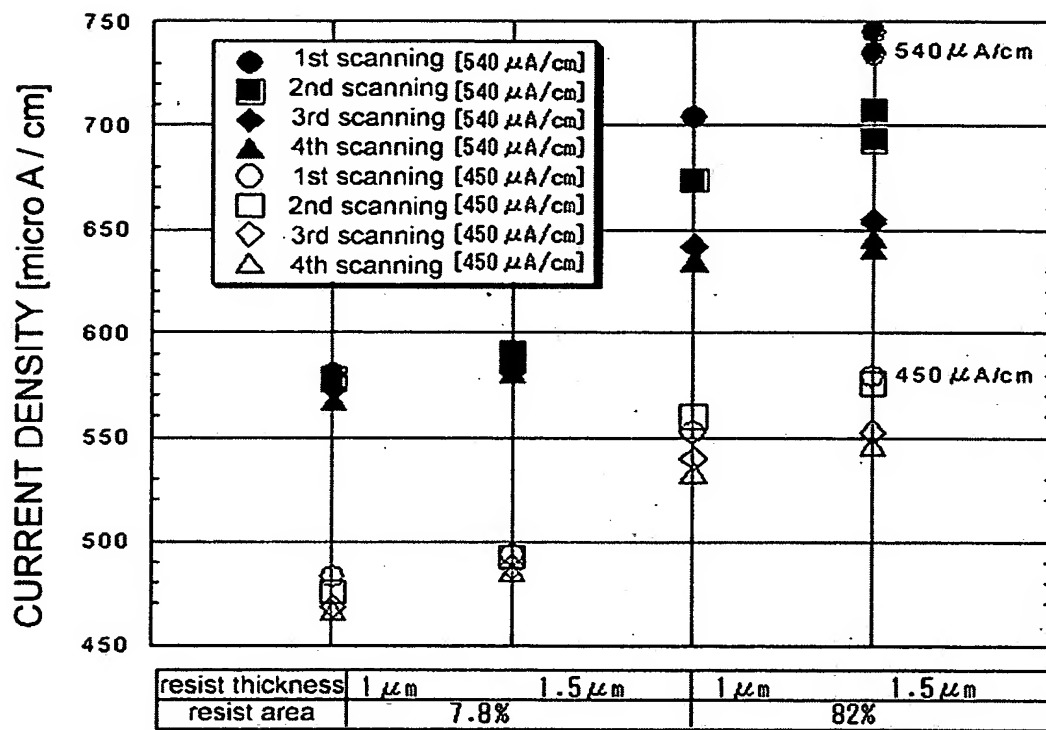


FIG. 4



RESIST FILM THICKNESS CONDITION  
(RESIST BAKING 250C 1hr.)

FIG. 5



RESIST FILM THICKNESS CONDITION  
(RESIST BAKING 250C 1hr.)

FIG. 6

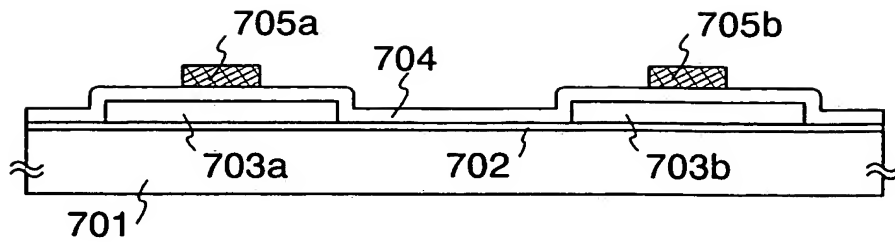


FIG. 7A

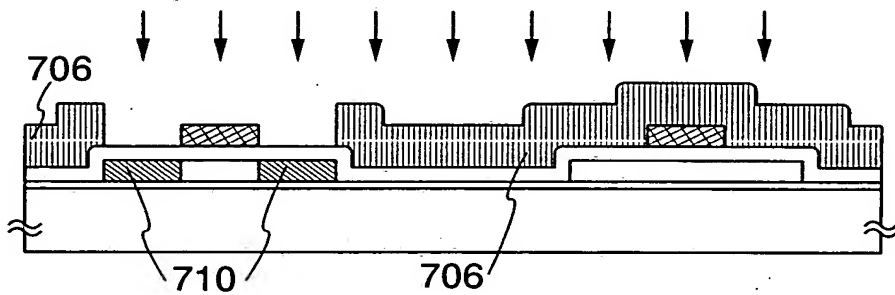


FIG. 7B Adding N-type Impurity Element (Phosphorus Doping)

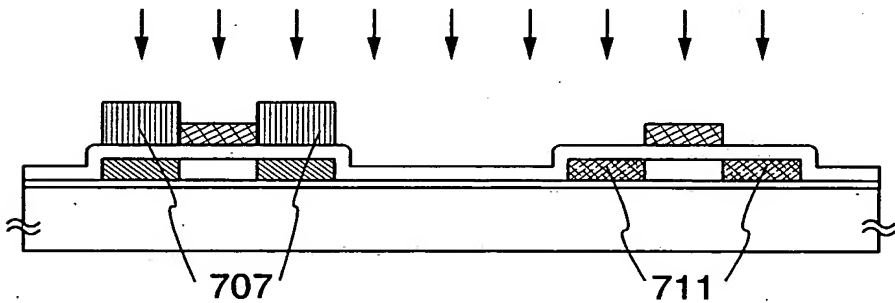


FIG. 7C Adding P-type Impurity Element (Boron Doping)

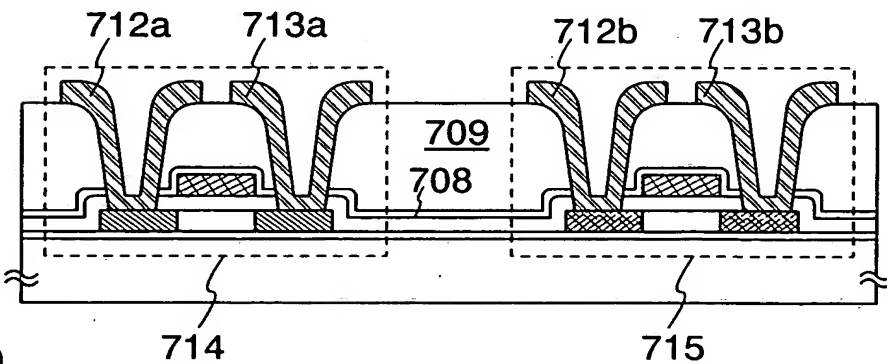


FIG. 7D

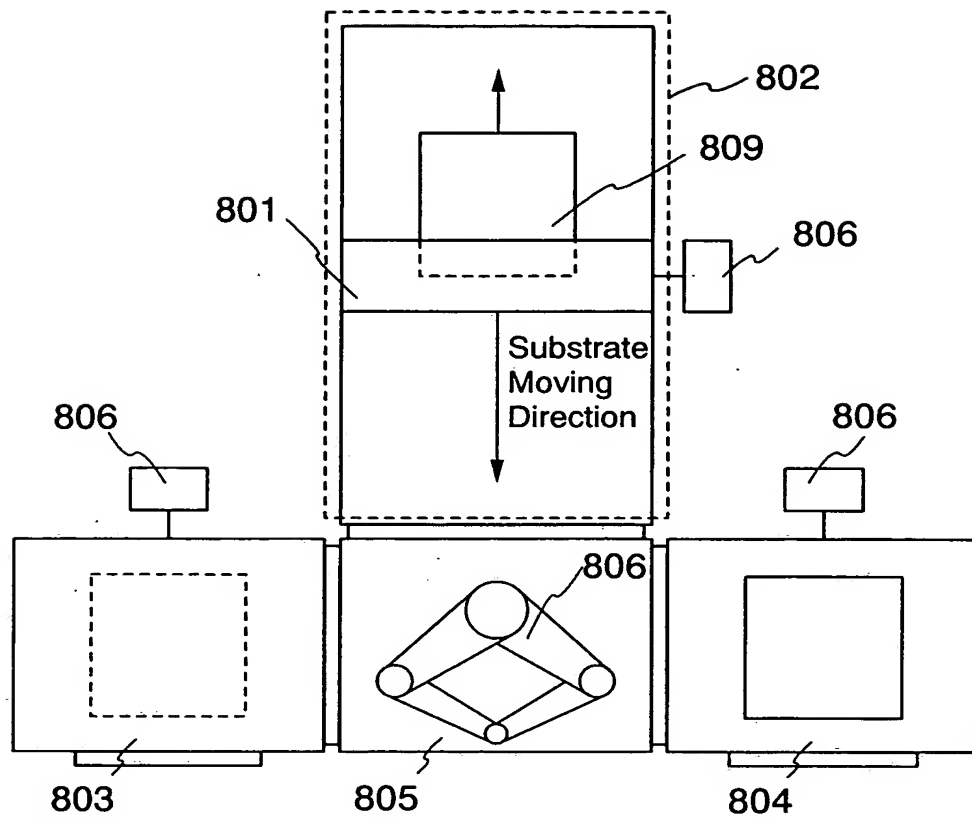


FIG. 8A

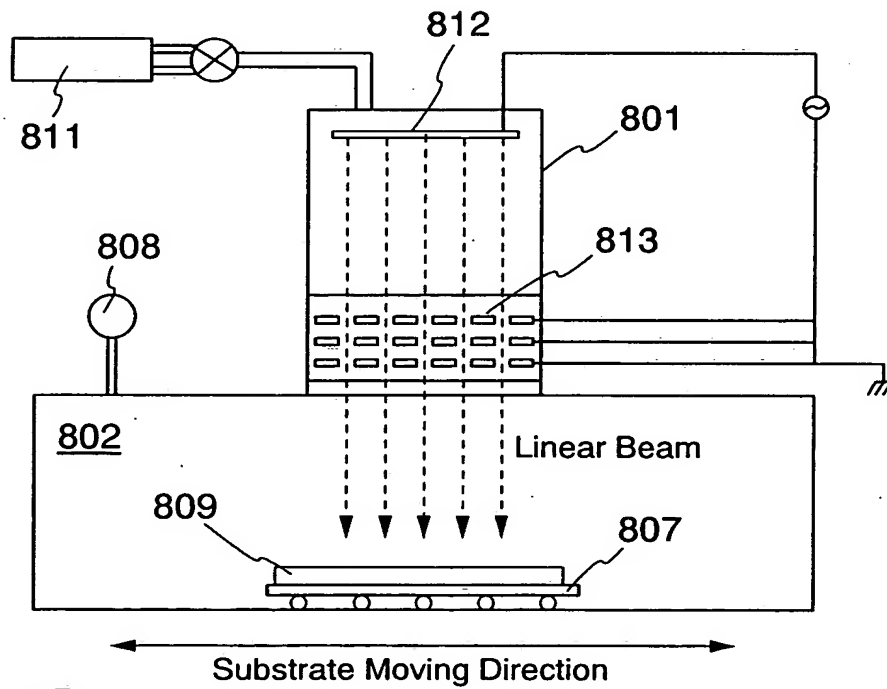


FIG. 8B

### Mask Pattern for Adding N-type Impurity Elements

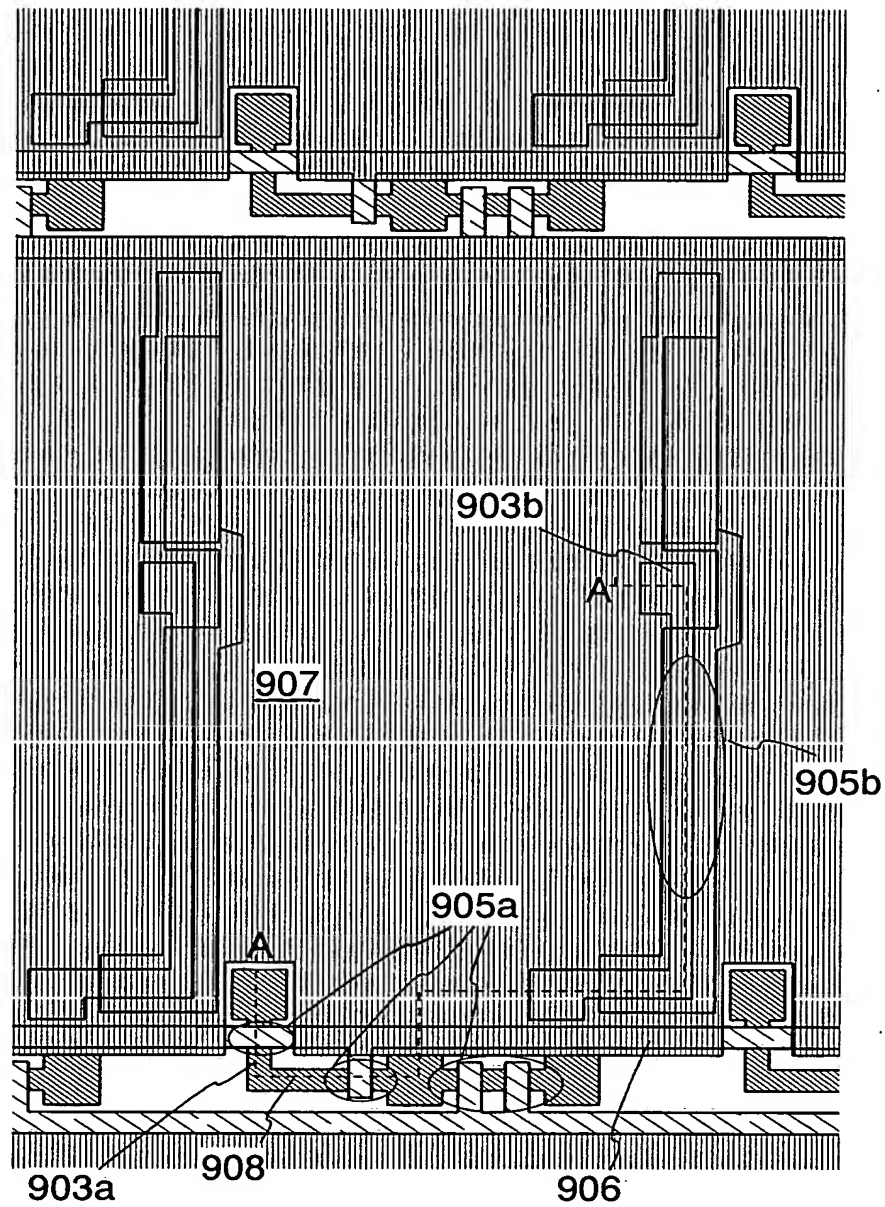


FIG. 9A

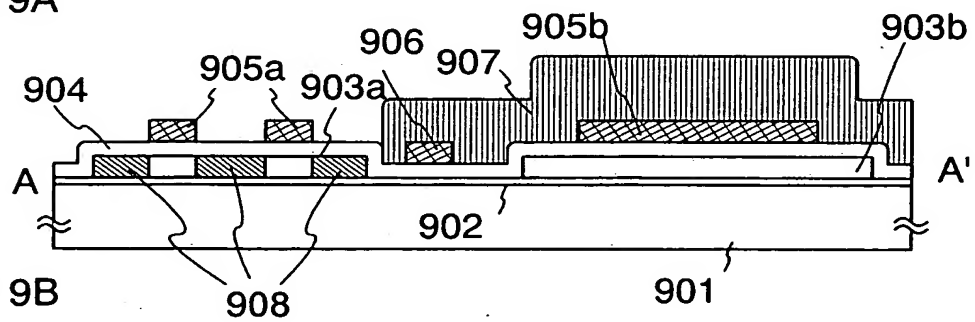


FIG. 9B

# Mask Pattern for Adding P-type Impurity Elements

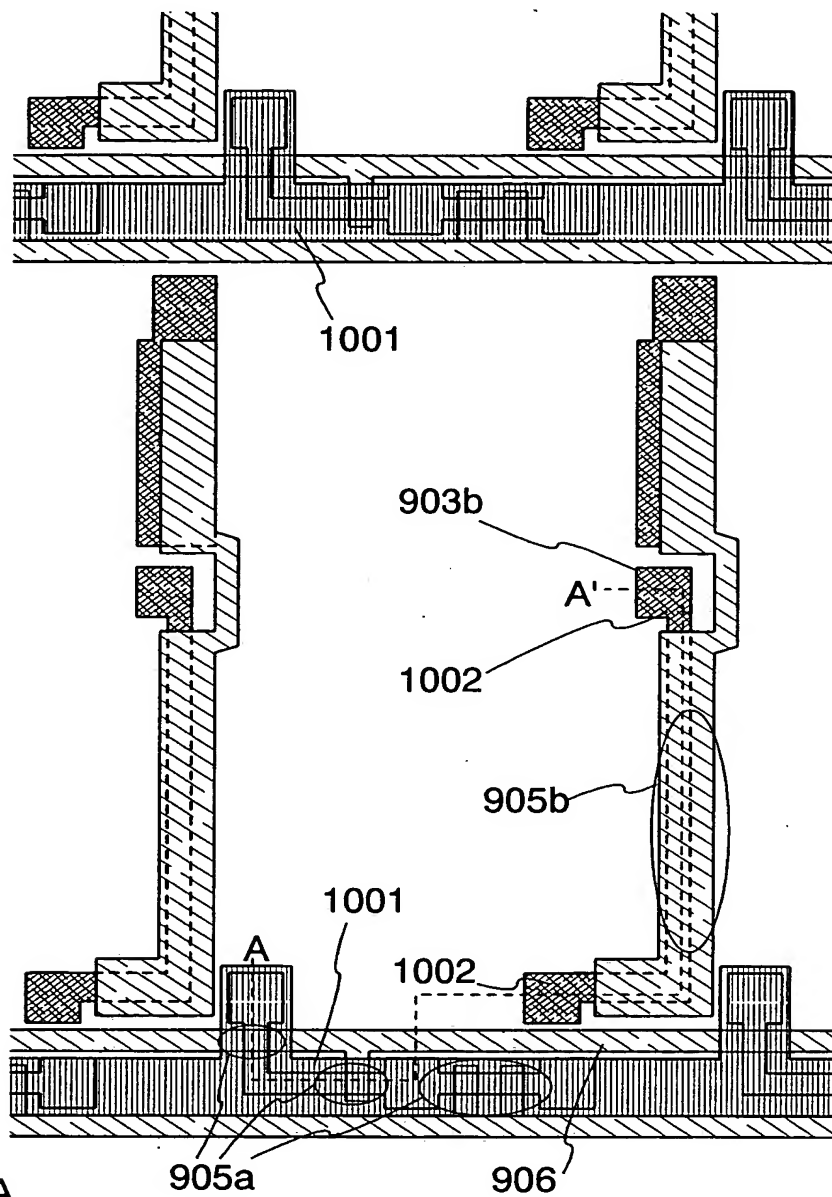


FIG. 10A

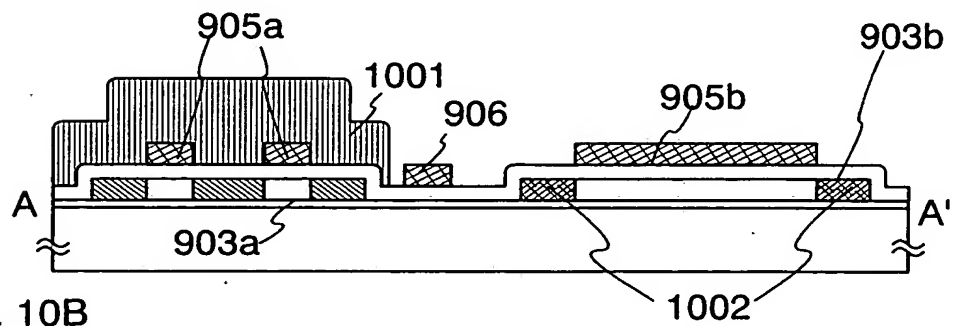


FIG. 10B

Condition after Carrying out Doping

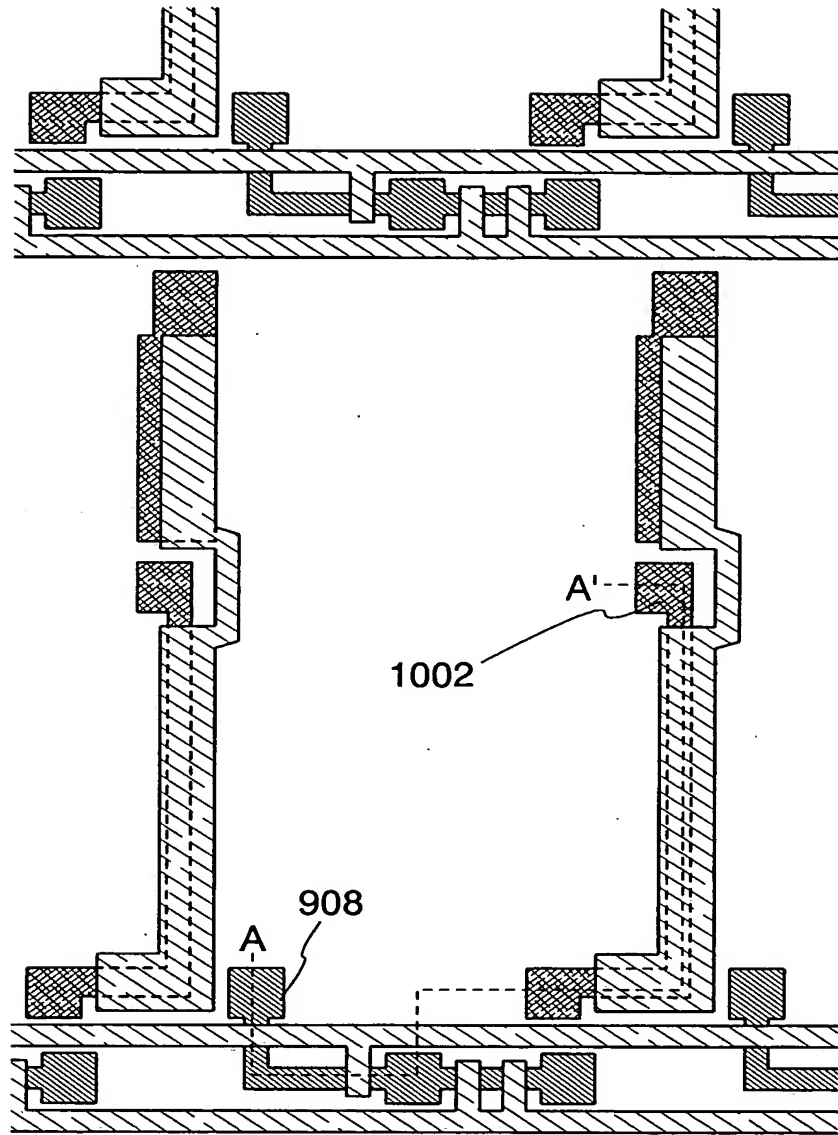


FIG. 11A

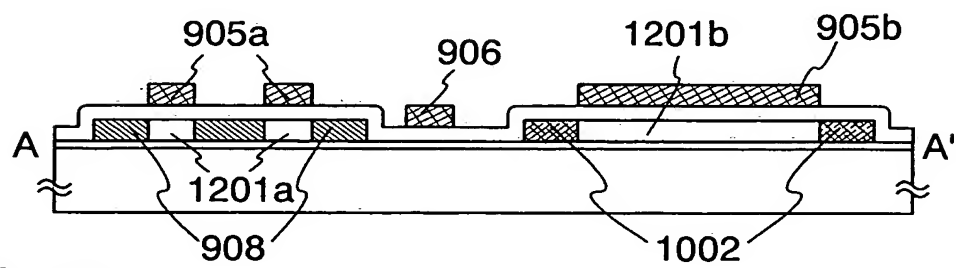


FIG. 11B

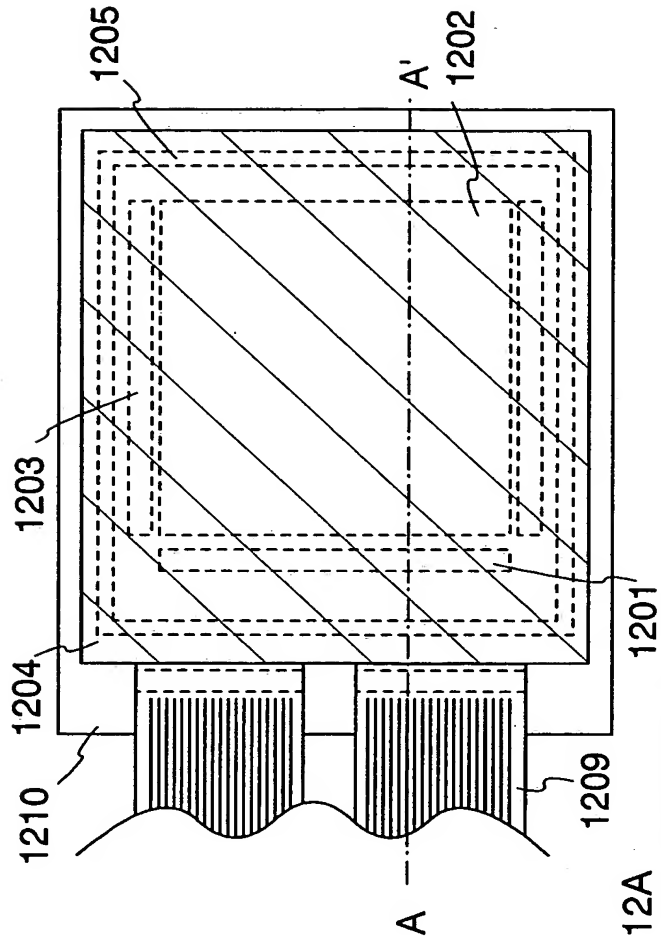


FIG. 12A

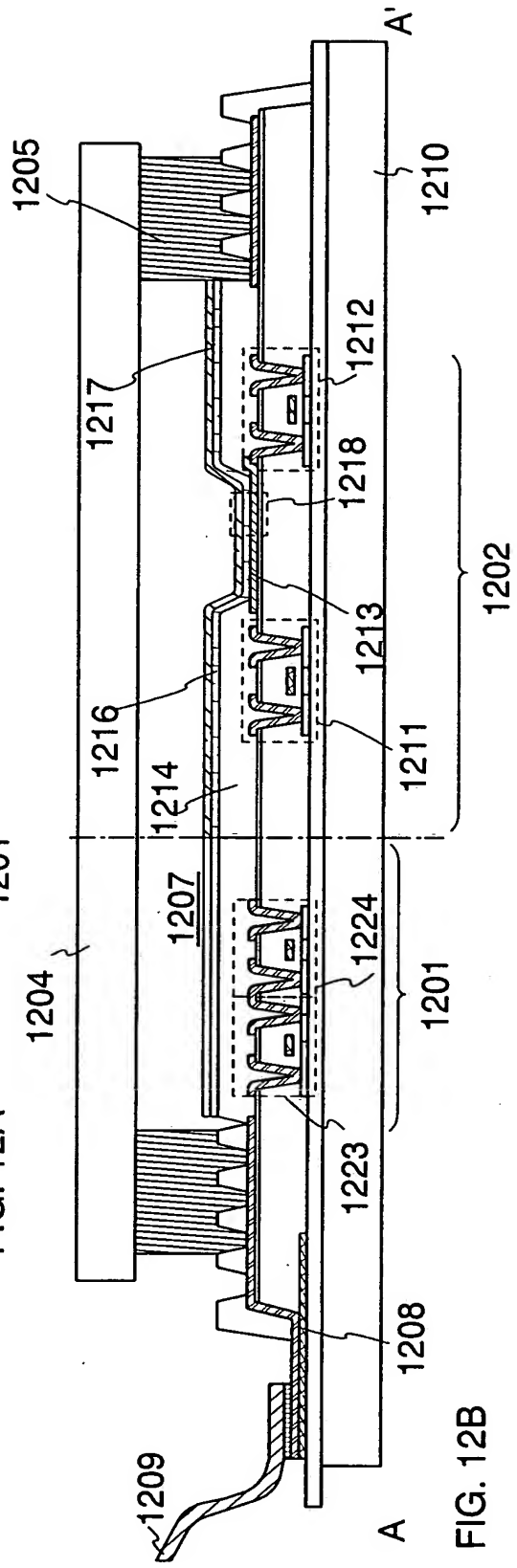


FIG. 12B

